

## 3rd Workshop on Advanced Silicon Radiation Detectors (3D and P-type Technologies)

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# Systematic measurements of p and n type diodes irradiated with protons, pions and neutrons

*Monday, 14 April 2008 15:00 (30 minutes)*

A large set of diodes processed by Micron on MCz and FZ n and p type materials was investigated up to equivalent fluences of  $3 \times 10^{15} \text{ cm}^{-2}$ . Charge collection measurements were performed in addition to C-V. The charge collection efficiency was found to be better than expected from simulations and good agreement was found between full depletion voltages determined from charge collection and CV measurements.

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